


## Small Outline Optoisolators Transistor Output

These devices consist of a gallium arsenide infrared emitting diode optically coupled to a monolithic silicon phototransistor detector, in a surface mountable, small outline, plastic package. They are ideally suited for high density applications, and eliminate the need for through-the-board mounting.

- Convenient Plastic SOIC-8 Surface Mountable Package Style
  - Standard SOIC-8 Footprint, with 0.050" Lead Spacing
- Compatible with Dual Wave, Vapor Phase and IR Reflow Soldering
- High Input-Output Isolation of 3000 Vac (rms) Guaranteed
- UL Recognized  File #E90700, Volume 2

### Ordering Information:

- To obtain MOC211, 212 and 213 in Tape and Reel, add R2 suffix to device numbers:  
R2 = 2500 units on 13" reel
- To obtain MOC211, 212 and 213 in quantities of 50 (shipped in sleeves) — No Suffix

### Marking Information:

- MOC211 = 211
- MOC212 = 212
- MOC213 = 213

### Applications:

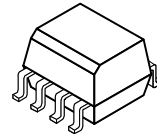
- General Purpose Switching Circuits
- Interfacing and coupling systems of different potentials and impedances
- Regulation Feedback Circuits
- Monitor and Detection Circuits

### MAXIMUM RATINGS (T<sub>A</sub> = 25°C unless otherwise noted)

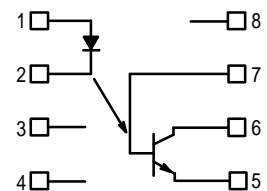
Rating	Symbol	Value	Unit
<b>INPUT LED</b>			
Forward Current — Continuous	I <sub>F</sub>	60	mA
Forward Current — Peak (PW = 100 μs, 120 pps)	I <sub>F(pk)</sub>	1.0	A
Reverse Voltage	V <sub>R</sub>	6.0	V
LED Power Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	90 0.8	mW mW/°C
<b>OUTPUT TRANSISTOR</b>			
Collector-Emitter Voltage	V <sub>CEO</sub>	30	V
Collector-Base Voltage	V <sub>CB0</sub>	70	V
Emitter-Collector Voltage	V <sub>ECO</sub>	7.0	V
Collector Current — Continuous	I <sub>C</sub>	150	mA
Detector Power Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	150 1.76	mW mW/°C

**MOC211**  
**MOC212**  
**MOC213**

**SMALL OUTLINE  
OPTOISOLATORS  
TRANSISTOR OUTPUT**



### SCHEMATIC



1. LED ANODE
2. LED CATHODE
3. NO CONNECTION
4. NO CONNECTION
5. EMITTER
6. COLLECTOR
7. BASE
8. NO CONNECTION

**MAXIMUM RATINGS — continued** ( $T_A = 25^\circ\text{C}$  unless otherwise noted)

Rating	Symbol	Value	Unit
<b>TOTAL DEVICE</b>			
Input–Output Isolation Voltage <sup>(1,2)</sup> (60 Hz, 1.0 sec. duration)	$V_{ISO}$	3000	Vac(rms)
Total Device Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	250 2.94	mW mW/ $^\circ\text{C}$
Ambient Operating Temperature Range <sup>(3)</sup>	$T_A$	–45 to +100	$^\circ\text{C}$
Storage Temperature Range <sup>(3)</sup>	$T_{stg}$	–45 to +125	$^\circ\text{C}$
Lead Soldering Temperature (1/16" from case, 10 sec. duration)	—	260	$^\circ\text{C}$

**ELECTRICAL CHARACTERISTICS** ( $T_A = 25^\circ\text{C}$  unless otherwise noted)<sup>(4)</sup>

Characteristic	Symbol	Min	Typ <sup>(4)</sup>	Max	Unit
<b>INPUT LED</b>					
Forward Voltage ( $I_F = 10\text{ mA}$ )	$V_F$	—	1.15	1.5	V
Reverse Leakage Current ( $V_R = 6.0\text{ V}$ )	$I_R$	—	0.1	100	$\mu\text{A}$
Capacitance	$C$	—	18	—	pF

**OUTPUT TRANSISTOR**

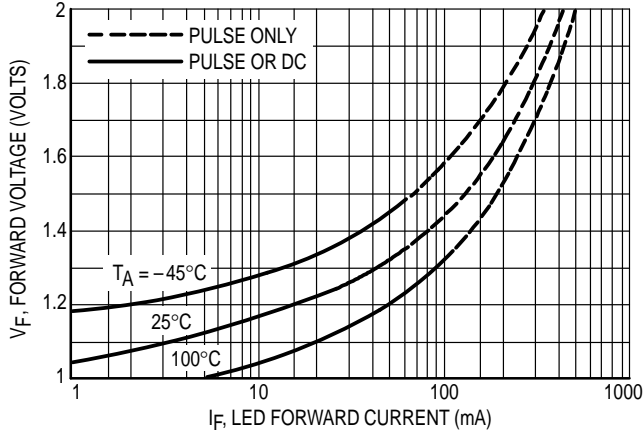
Collector–Emitter Dark Current ( $V_{CE} = 10\text{ V}$ , $T_A = 25^\circ\text{C}$ ) ( $V_{CE} = 10\text{ V}$ , $T_A = 100^\circ\text{C}$ )	$I_{CEO1}$	—	1.0	50	nA
	$I_{CEO2}$	—	1.0	—	$\mu\text{A}$
Collector–Emitter Breakdown Voltage ( $I_C = 100\ \mu\text{A}$ )	$V_{(BR)CEO}$	30	90	—	V
Emitter–Collector Breakdown Voltage ( $I_E = 100\ \mu\text{A}$ )	$V_{(BR)ECO}$	7.0	7.8	—	V
Collector–Emitter Capacitance ( $f = 1.0\text{ MHz}$ , $V_{CE} = 0$ )	$C_{CE}$	—	7.0	—	pF

**COUPLED**

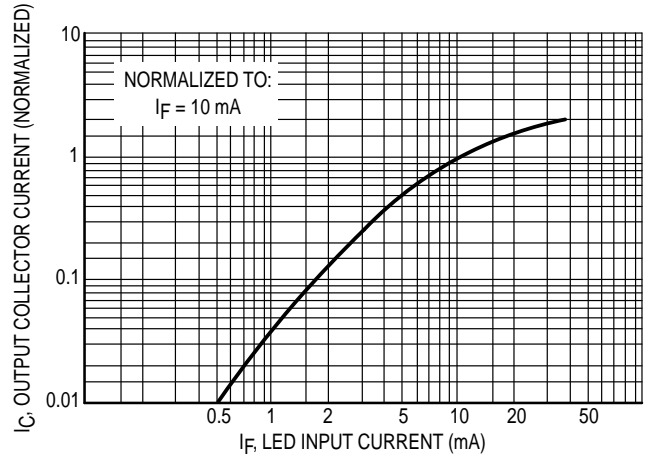
Output Collector Current ( $I_F = 10\text{ mA}$ , $V_{CE} = 10\text{ V}$ )	MOC211 MOC212 MOC213	$I_C$ (CTR) <sup>(5)</sup>	2.0 (20) 5.0 (50) 10 (100)	6.5 (65) 9.0 (90) 14 (140)	— — —	mA (%)
Collector–Emitter Saturation Voltage ( $I_C = 2.0\text{ mA}$ , $I_F = 10\text{ mA}$ )		$V_{CE(sat)}$	—	0.15	0.4	V
Turn–On Time ( $I_C = 2.0\text{ mA}$ , $V_{CC} = 10\text{ V}$ , $R_L = 100\ \Omega$ )		$t_{on}$	—	7.5	—	$\mu\text{s}$
Turn–Off Time ( $I_C = 2.0\text{ mA}$ , $V_{CC} = 10\text{ V}$ , $R_L = 100\ \Omega$ )		$t_{off}$	—	5.7	—	$\mu\text{s}$
Rise Time ( $I_C = 2.0\text{ mA}$ , $V_{CC} = 10\text{ V}$ , $R_L = 100\ \Omega$ )		$t_r$	—	3.2	—	$\mu\text{s}$
Fall Time ( $I_C = 2.0\text{ mA}$ , $V_{CC} = 10\text{ V}$ , $R_L = 100\ \Omega$ )		$t_f$	—	4.7	—	$\mu\text{s}$
Input–Output Isolation Voltage ( $f = 60\text{ Hz}$ , $t = 1.0\text{ sec.}$ ) <sup>(1,2)</sup>		$V_{ISO}$	3000	—	—	Vac(rms)
Isolation Resistance ( $V_{I-O} = 500\text{ V}$ ) <sup>(2)</sup>		$R_{ISO}$	$10^{11}$	—	—	$\Omega$
Isolation Capacitance ( $V_{I-O} = 0$ , $f = 1.0\text{ MHz}$ ) <sup>(2)</sup>		$C_{ISO}$	—	0.2	—	pF

1. Input–Output Isolation Voltage,  $V_{ISO}$ , is an internal device dielectric breakdown rating.
2. For this test, pins 1 and 2 are common, and pins 5, 6 and 7 are common.
3. Refer to Quality and Reliability Section in Opto Data Book for information on test conditions.
4. Always design to the specified minimum/maximum electrical limits (where applicable).
5. Current Transfer Ratio (CTR) =  $I_C/I_F \times 100\%$ .

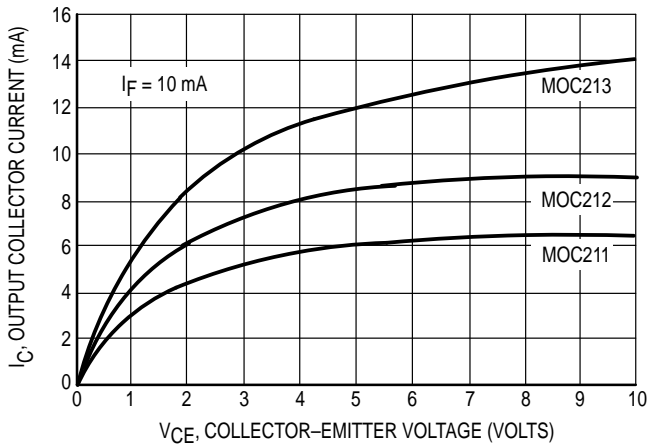
**TYPICAL CHARACTERISTICS**



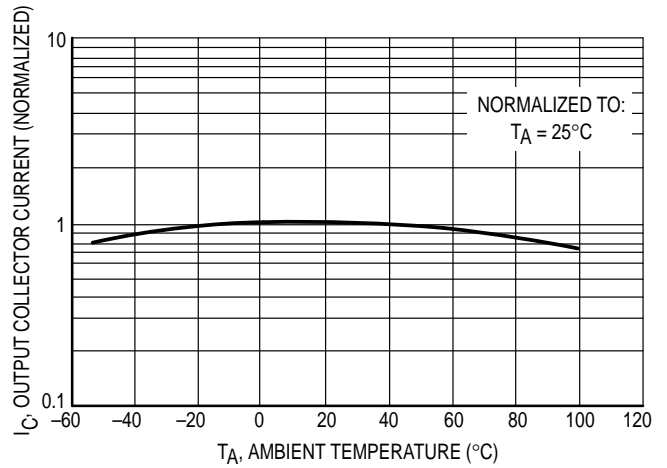
**Figure 1. LED Forward Voltage versus Forward Current**



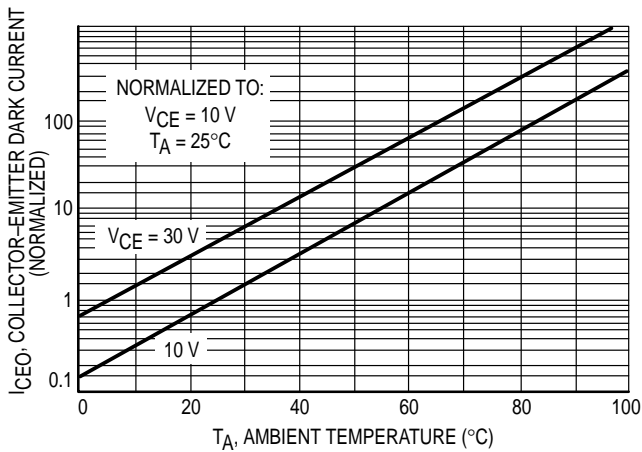
**Figure 2. Output Current versus Input Current**



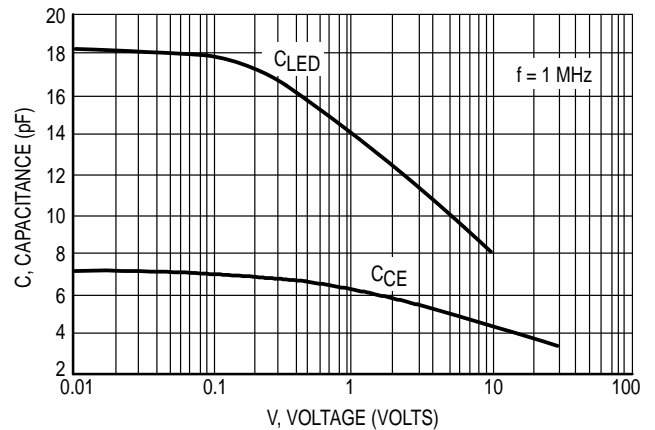
**Figure 3. Output Current versus Collector-Emitter Voltage**



**Figure 4. Output Current versus Ambient Temperature**

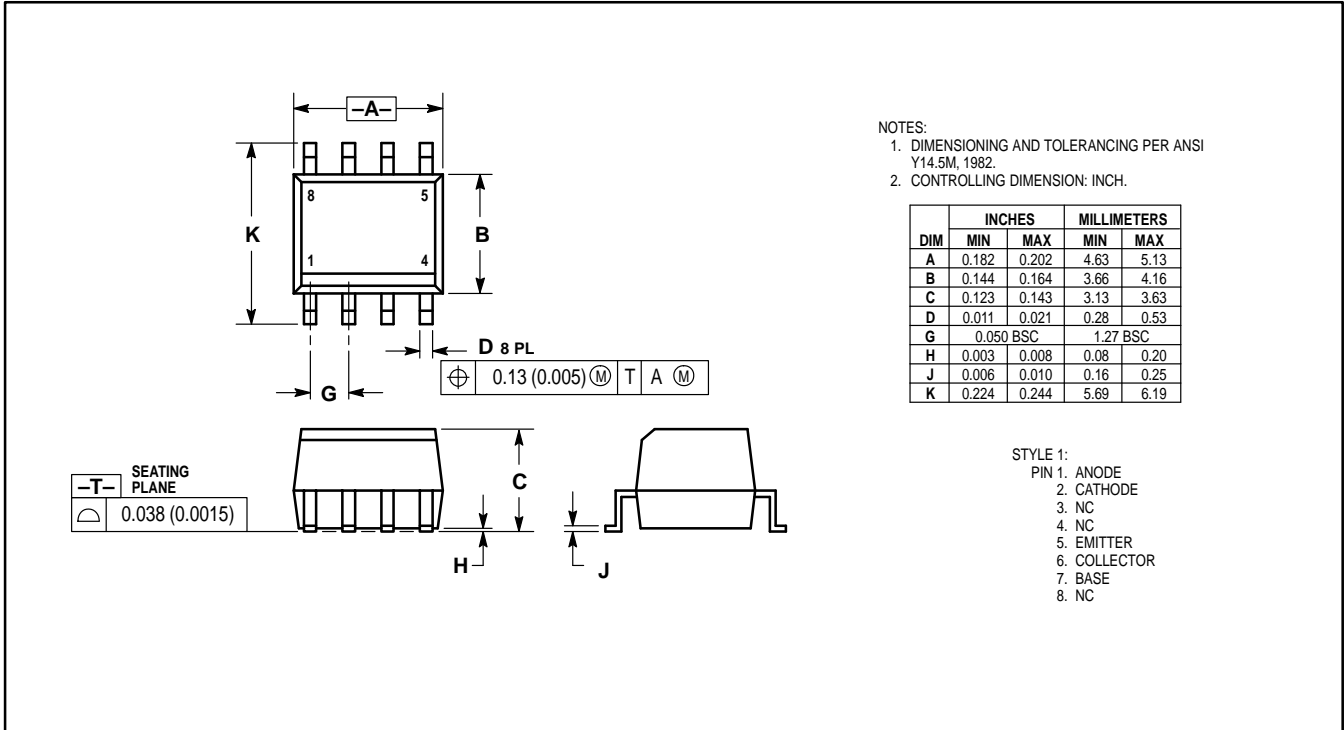


**Figure 5. Dark Current versus Ambient Temperature**



**Figure 6. Capacitance versus Voltage**

**PACKAGE DIMENSIONS**



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2. A critical component in any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.